

NPN SWITCHING TRANSISTOR

- STMicroelectronics PREFERRED SALESTYPE
- NPN TRANSISTOR
- VERY LOW SATURATION VOLTAGE
- FAST TURN-OFF AND TURN-ON

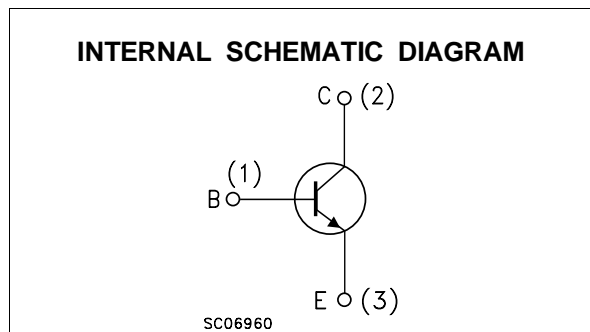
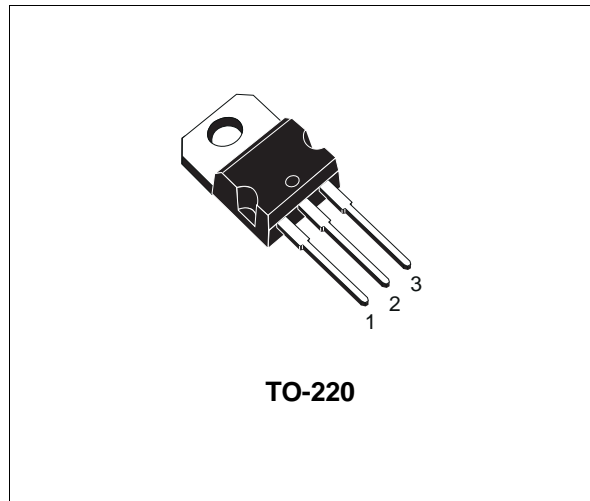
APPLICATIONS:

- SWITCHING REGULATORS
- SOLENOID / RELAY DRIVERS

DESCRIPTION

High speed transistor suited for low voltage applications.

High frequency and efficiency converters switching regulators motor control.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-base Voltage ($I_E = 0$)	400	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	200	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	7	V
I_C	Collector Current	10	A
I_{CM}	Collector Peak Current ($t_p < 5ms$)	15	A
I_B	Base Current	2	A
I_{BM}	Base Peak Current ($t_p < 5ms$)	4	A
P_{tot}	Total Dissipation at $T_c < 25\text{ }^\circ\text{C}$	85	W
P_{tot}	Total Dissipation at $T_c < 60\text{ }^\circ\text{C}$	65	W
T_{stg}	Storage Temperature	-65 to +175	$^\circ\text{C}$
T_j	Max. Operating Junction Temperature	175	$^\circ\text{C}$

BUV28

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	1.76	°C/W
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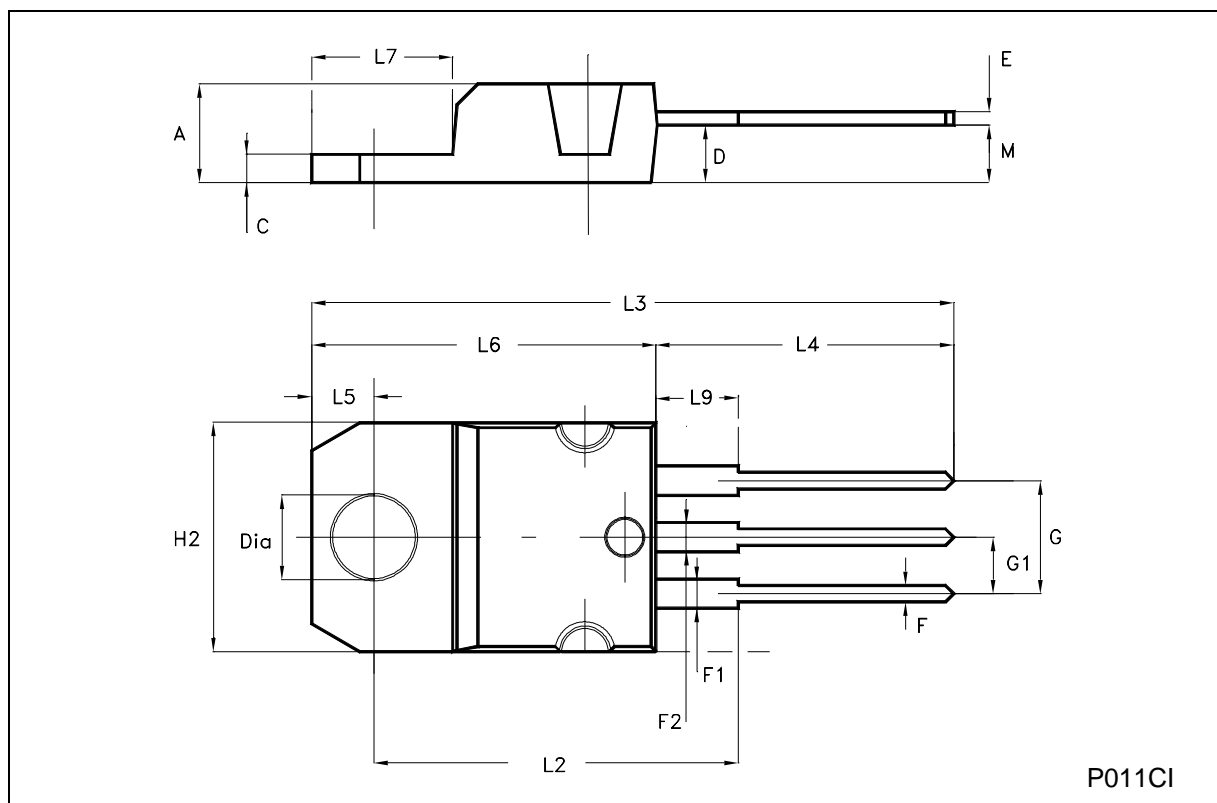
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CEr}	Collector Cut-off Current (R _{BE} = 50Ω)	V _{CE} = 400V T _c = 125°C			3	mA
I _{CEX}	Collector Cut-off Current (V _{BE} = -1.5V)	V _{CE} = 400V T _c = 125°C			1	mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			1	mA
V _{CEO(sus)*}	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 0.2 A	200			V
V _{EBO}	Emitter-Base Voltage (I _C = 0)	I _E = 50 mA	7		30	V
V _{CE(sat)*}	Collector-Emitter Saturation Voltage	I _C = 3 A I _B = 0.3 A I _C = 6 A I _B = 0.6 A			0.7 1.5	V V
V _{BE(sat)*}	Base-Emitter Saturation Voltage	I _C = 6 A I _B = 0.6 A			2	V
t _{on} t _s t _f	RESISTIVE LOAD Storage Time Fall Time Turn-on Time	V _{CC} = 150 V I _C = 6 A V _{BE} = - 6 V I _{B1} = 0.6 A R _{BB} = 5 Ω I _{B2} = - 1.2 A			1 1.5 0.25	μs μs μs
t _s t _f	INDUCTIVE LOAD Storage Time Fall Time	V _{CC} = 150 V I _C = 6 A I _{B1} = 0.6 A V _{BE} = - 5 V L _B = 3 μH T _c = 125 °C			3 0.2	μs μs

* Pulsed: Pulse duration = 300μs, duty cycle = 2 %

TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.052
D	2.40		2.72	0.094		0.107
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.202
G1	2.40		2.70	0.094		0.106
H2	10.00		10.40	0.394		0.409
L2		16.40			0.645	
L4	13.00		14.00	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.20		6.60	0.244		0.260
L9	3.50		3.93	0.137		0.154
M		2.60			0.102	
DIA.	3.75		3.85	0.147		0.151



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